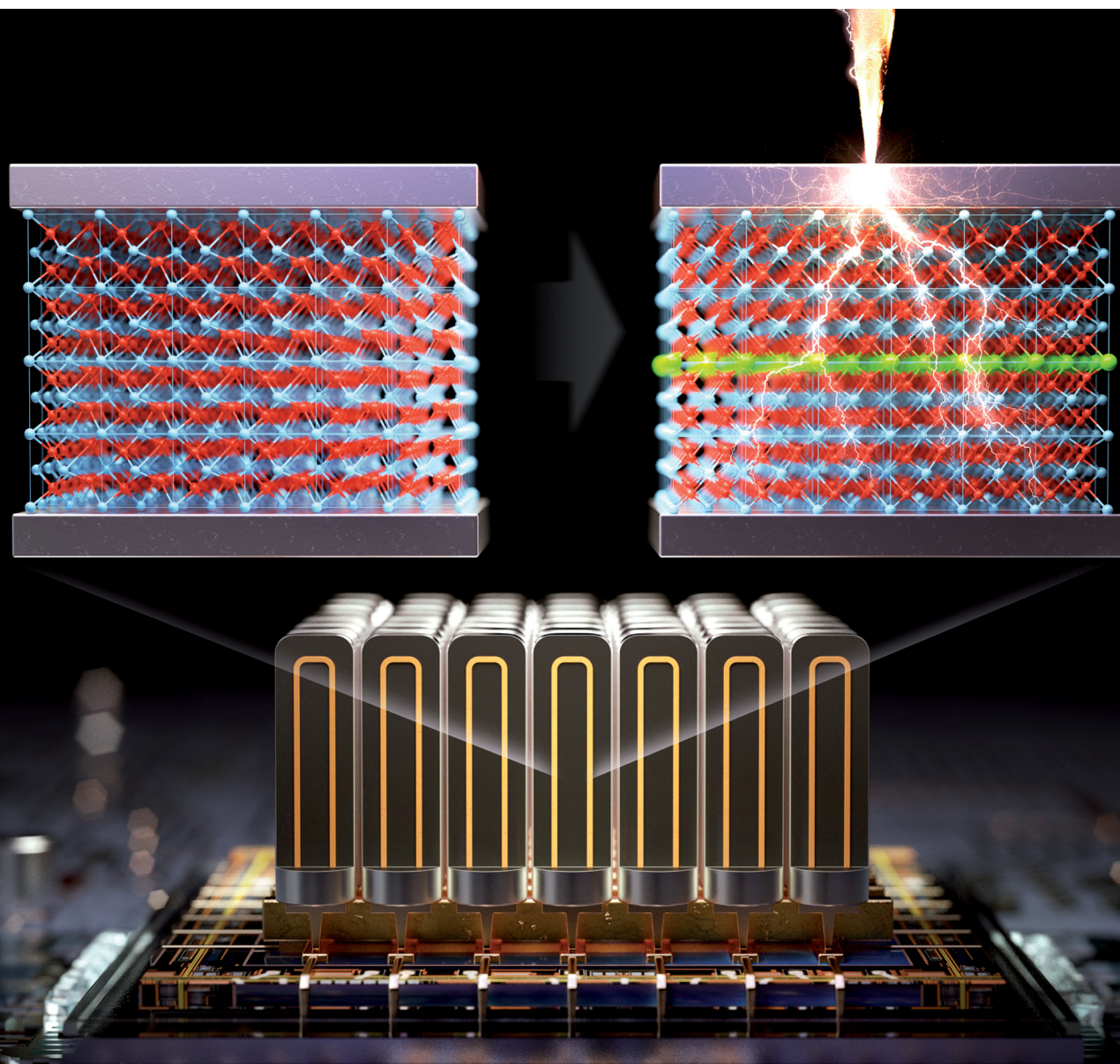


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Cheol Seong Hwang *et al.*
High-performance dynamic random access memory capacitor with an equivalent oxide thickness of 0.31 nm *via* stepwise cycling in Y-doped $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ thin films